PTO-1449

Information Disclosure Citation in an Application

Application No. unknown

Applicant(s)
Scott R. Runnels

Docket Number 090936.0395 Group Art Unit unknown 212) Filing Date
October 24, 2000

U.S. PATENT DOCUMENTS

		DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
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EXAMINER

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.



PTO-1449				Application No. unknown	Applicant(s) Scott R. Ru	ınnels					
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